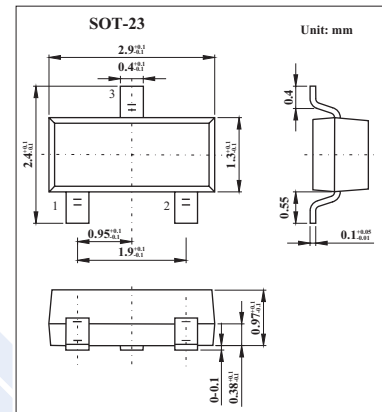
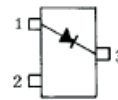


Silicon Epitaxial Planar Type

1SS307

■ Features

- Low forward voltage : $V_F = 1.0$ V(Typ)
- Low reverse Current : $I_R = 0.1$ nA (Typ)
- Small total capacitance : $C_T = 3.0$ pF(Typ)



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	35	V
Reverse voltage	V_R	30	V
Average forward current	I_O	100	mA
Maximum (peak) forward current	I_{FM}	300	mA
Surge current (10 ms)	I_{FSM}	2	A
Power dissipation	P	150	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 + 125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 100$ mA		1.0	1.3	V
Reverse current	I_R	$V_R = 30$ V		0.1	10	nA
Total capacitance	C_T	$V_R = 0, f = 1.0$ MHz		3.0	6.0	pF

■ Marking

Marking	C9
---------	----